

## CORRECTION

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## Correction: Electrical characteristics and photodetection mechanism of TiO<sub>2</sub>/AlGa<sub>0.3</sub>N/GaN heterostructure-based ultraviolet detectors with a Schottky junction

Teng Zhan,<sup>ac</sup> Jianwen Sun,<sup>b</sup> Tao Feng,<sup>ac</sup> Yulong Zhang,<sup>b</sup> Binru Zhou,<sup>ac</sup> Banghong Zhang,<sup>ac</sup> Junxi Wang,<sup>ac</sup> Pasqualina M. Sarro,<sup>d</sup> Guoqi Zhang,<sup>d</sup> Zewen Liu,<sup>\*b</sup> Xiaoyan Yi<sup>\*ac</sup> and Jinmin Li<sup>\*ac</sup>

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Correction for 'Electrical characteristics and photodetection mechanism of TiO<sub>2</sub>/AlGa<sub>0.3</sub>N/GaN heterostructure-based ultraviolet detectors with a Schottky junction' by Teng Zhan *et al.*, *J. Mater. Chem. C*, 2023, **11**, 1704–1713, <https://doi.org/10.1039/D2TC04491A>.

The authors regret an error in the abstract of the published article: the text “(i) the Schottky emission mechanism at a low reverse voltage (0–1 V) before the current is fully turned on.” should be changed to “(i) the Schottky emission mechanism at a low reverse voltage (0 to –1 V) before the current is fully turned on.” This change does not affect the main conclusions of the manuscript. The authors would like to apologize for any inconvenience caused.

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

<sup>a</sup> Research and Development Center for Solid State Lighting, Institute of Semiconductors, Chinese Academy of Sciences, Qinghua East Road 35A, 100083, Beijing, China. E-mail: spring@semi.ac.cn, jmli@semi.ac.cn

<sup>b</sup> School of Integrated Circuits, Tsinghua University, 100084, Beijing, China. E-mail: liuzw@tsinghua.edu.cn

<sup>c</sup> College of Materials Sciences and Opto-Electronic Technology, University of Chinese Academy of Sciences, No. 19A Yuquan Road, Beijing, 100049, China

<sup>d</sup> Department of Microelectronics, Delft University of Technology, 2628 CD Delft, The Netherlands

